

# High Voltage IGBT

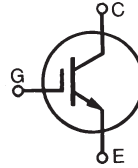
## For Capacitor Discharge Applications

# IXGT25N250HV

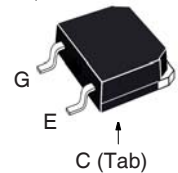
$$V_{CES} = 2500V$$

$$I_{C110} = 25A$$

$$V_{CE(sat)} \leq 2.9V$$



TO-268



G = Gate      C = Collector  
E = Emitter    Tab = Collector

Symbol	Test Conditions	Maximum Ratings	
$V_{CES}$	$T_J = 25^\circ\text{C}$ to $150^\circ\text{C}$	2500	V
$V_{CGR}$	$T_J = 25^\circ\text{C}$ to $150^\circ\text{C}$ , $R_{GE} = 1M\Omega$	2500	V
$V_{GES}$	Continuous	$\pm 20$	V
$V_{GEM}$	Transient	$\pm 30$	V
$I_{C25}$	$T_C = 25^\circ\text{C}$	60	A
$I_{C110}$	$T_C = 110^\circ\text{C}$	25	A
$I_{CM}$	$T_C = 25^\circ\text{C}$ , $V_{GE} = 20V$ , 1ms	200	A
<b>SSOA</b>	$V_{GE} = 20V$ , $T_{VJ} = 125^\circ\text{C}$ , $R_G = 20\Omega$	$I_{CM} = 240$	A
<b>(RBSOA)</b>	Clamped Inductive Load	$0.5 \cdot V_{CES}$	
$P_C$	$T_C = 25^\circ\text{C}$	250	W
$T_J$		-55 ... +150	$^\circ\text{C}$
$T_{JM}$		150	$^\circ\text{C}$
$T_{stg}$		-55 ... +150	$^\circ\text{C}$
$T_L$	1.6mm (0.062 in.) from Case for 10s	300	$^\circ\text{C}$
$T_{SOLD}$	Plastic Body for 10 seconds	260	$^\circ\text{C}$
<b>Weight</b>		4	g

### Features

- High Blocking Voltage
- High Voltage Package

### Advantages

- High Power Density
- Easy to Mount

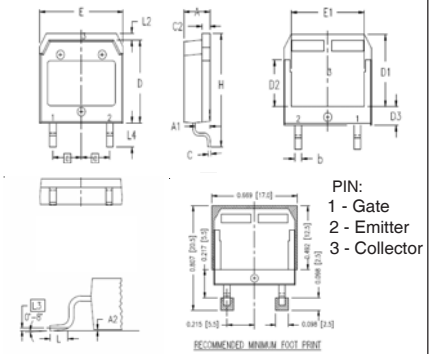
### Applications

- Capacitor Discharge
- Pulser Circuits

Symbol	Test Conditions ( $T_J = 25^\circ\text{C}$ , Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
$BV_{CES}$	$I_C = 250\mu\text{A}$ , $V_{GE} = 0V$	2500		V
$V_{GE(th)}$	$I_C = 250\mu\text{A}$ , $V_{CE} = V_{GE}$	3.0		5.0 V
$I_{CES}$	$V_{CE} = 0.8 \cdot V_{CES}$ , $V_{GE} = 0V$ $T_J = 125^\circ\text{C}$			50 $\mu\text{A}$ 1 mA
$I_{GES}$	$V_{CE} = 0V$ , $V_{GE} = \pm 20V$			$\pm 100$ nA
$V_{CE(sat)}$	$I_C = 25A$ , $V_{GE} = 15V$ , Note 1 $I_C = 75A$			2.9 V 5.2 V

Symbol	Test Conditions ( $T_J = 25^\circ\text{C}$ , Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
$g_{fs}$	$I_C = 50\text{A}$ , $V_{CE} = 10\text{V}$ , Note 1	16	26	S
$I_{C(ON)}$	$V_{GE} = 15\text{V}$ , $V_{CE} = 20\text{V}$ , Note 1		240	A
$C_{ies}$	$V_{CE} = 25\text{V}$ , $V_{GE} = 0\text{V}$ , $f = 1\text{MHz}$		2310	pF
$C_{oes}$			75	pF
$C_{res}$			23	pF
$Q_g$	$I_C = 50\text{A}$ , $V_{GE} = 15\text{V}$ , $V_{CE} = 0.5 \cdot V_{CES}$		75	nC
$Q_{ge}$			15	nC
$Q_{gc}$			30	nC
$t_{d(on)}$	<b>Resistive Switching Times</b> $I_C = 50\text{A}$ , $V_{GE} = 15\text{V}$ $V_{CE} = 1250\text{V}$ , $R_G = 5\Omega$		68	ns
$t_r$			233	ns
$t_{d(off)}$			209	ns
$t_f$			200	ns
$R_{thJC}$				0.50 $^\circ\text{C/W}$

### TO-268 (VHV) Outline



SYM	INCHES		MILLIMETER	
	MIN	MAX	MIN	MAX
A	.193	.201	4.90	5.10
A1	.106	.114	2.70	2.90
A2	.001	.010	0.02	0.25
b	.045	.057	1.15	1.45
C	.016	.026	0.40	0.65
C2	.057	.063	1.45	1.60
D	.543	.551	13.80	14.00
D1	.465	.476	11.80	12.10
D2	.295	.307	7.50	7.80
D3	.114	.126	2.90	3.20
E	.624	.632	15.85	16.05
E1	.524	.535	13.30	13.60
$\text{[E]}$	.215	BSC	5.45	BSC
H	.736	.752	18.70	19.10
L	.067	.079	1.70	2.00
L2	.039	.045	1.00	1.15
$\text{[L3]}$	.010	BSC	0.25	BSC
L4	.150	.161	3.80	4.10

Note 1. Pulse test,  $t < 300\mu\text{s}$ , duty cycle,  $d < 2\%$ .

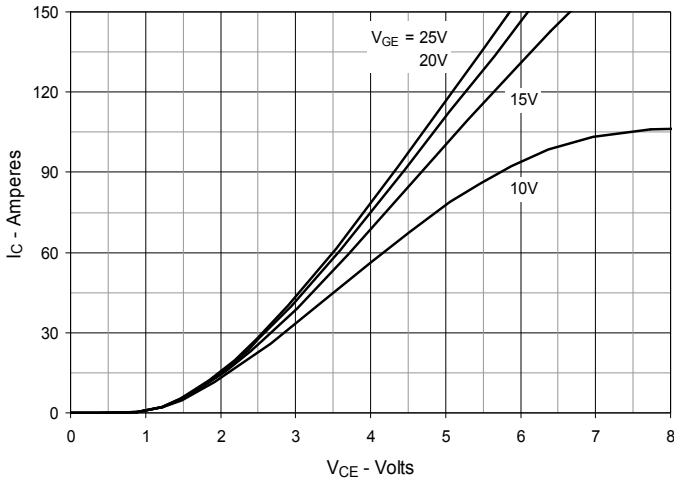
### ADVANCE TECHNICAL INFORMATION

The product presented herein is under development. The Technical Specifications offered are derived from a subjective evaluation of the design, based upon prior knowledge and experience, and constitute a "considered reflection" of the anticipated result. IXYS reserves the right to change limits, test conditions, and dimensions without notice.

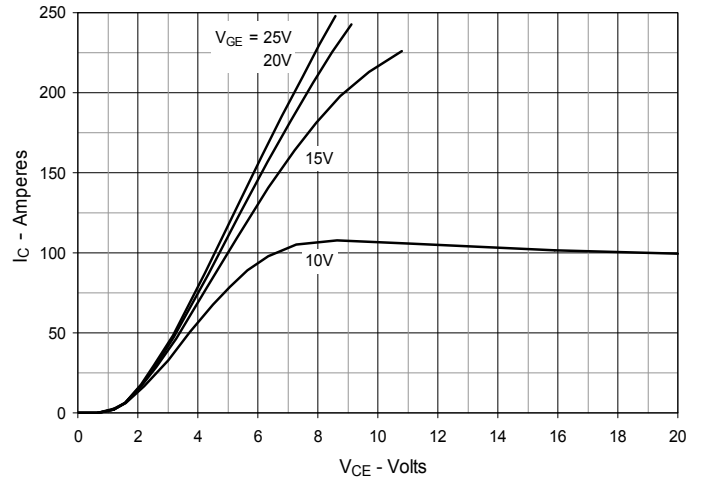
IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:	4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338B2
	4,860,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
	4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	

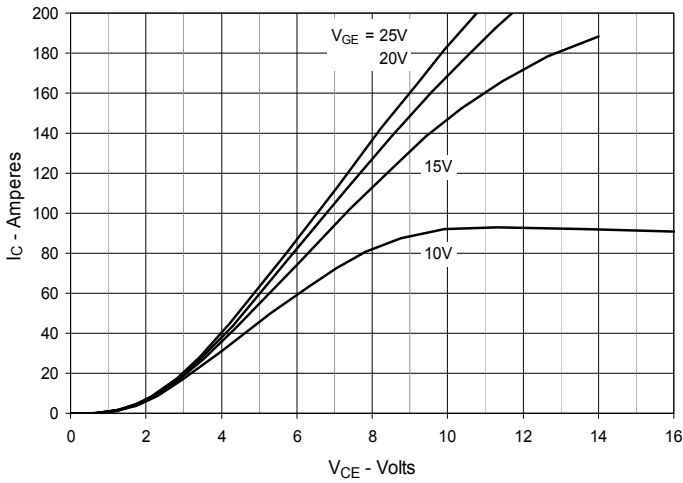
**Fig. 1. Output Characteristics @  $T_J = 25^\circ\text{C}$**



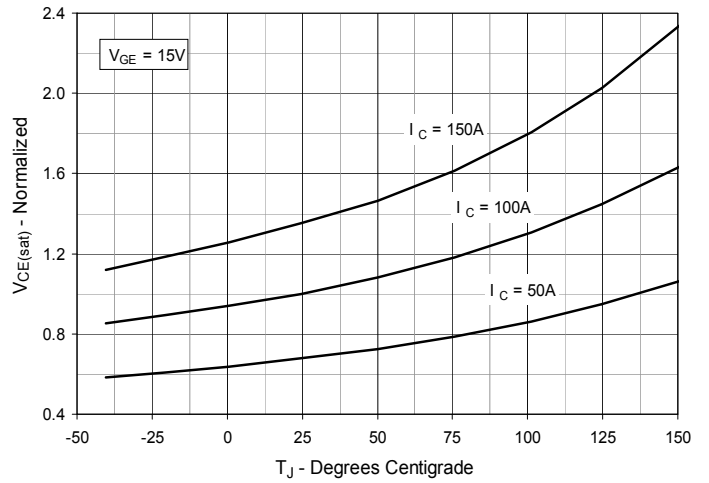
**Fig. 2. Extended Output Characteristics @  $T_J = 25^\circ\text{C}$**



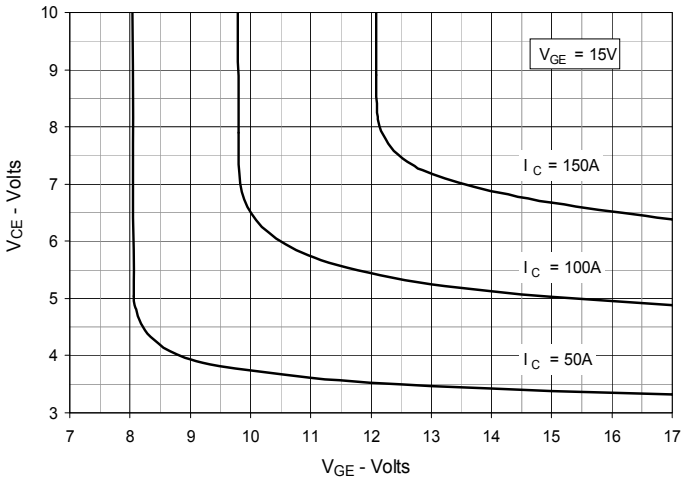
**Fig. 3. Output Characteristics @  $T_J = 125^\circ\text{C}$**



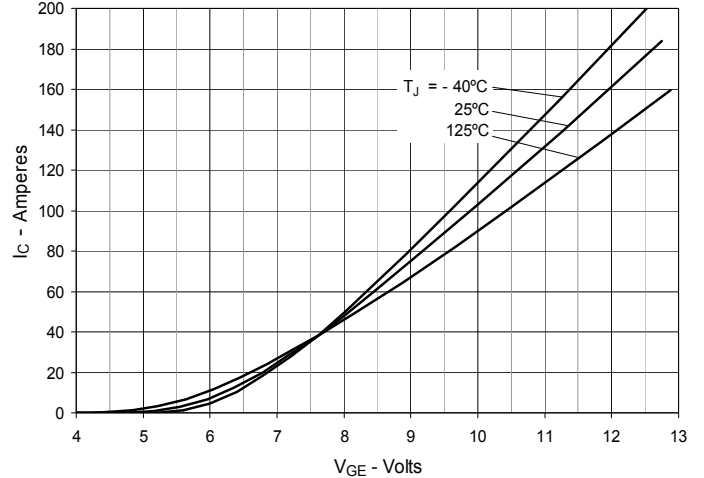
**Fig. 4. Dependence of  $V_{CE(sat)}$  on Junction Temperature**



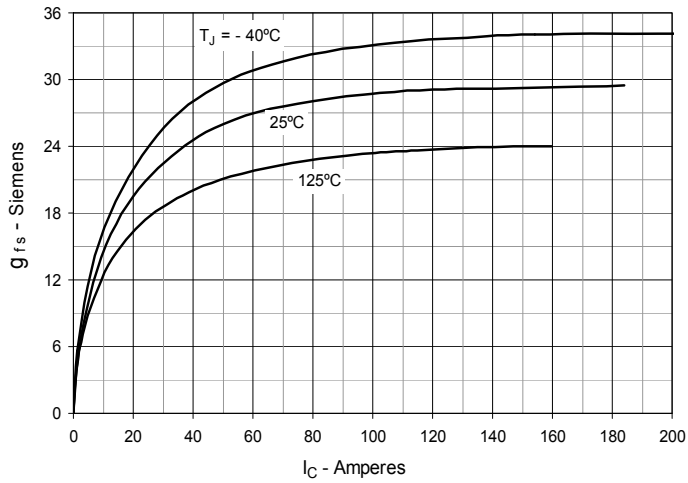
**Fig. 5. Collector-to-Emitter Voltage vs. Gate-to-Emitter Voltage**



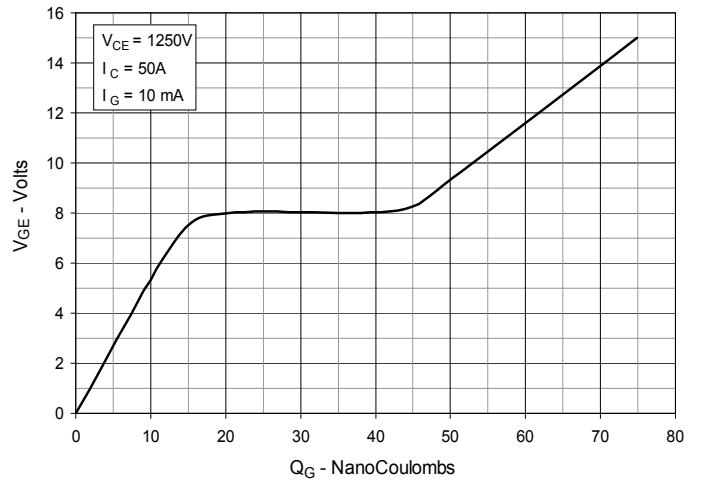
**Fig. 6. Input Admittance**



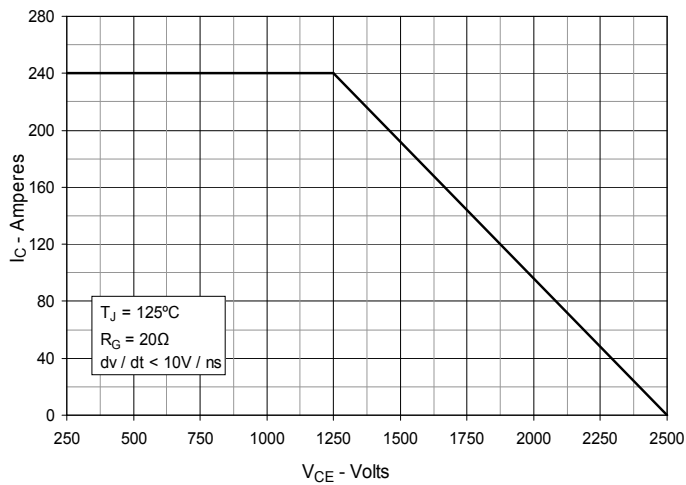
**Fig. 7. Transconductance**



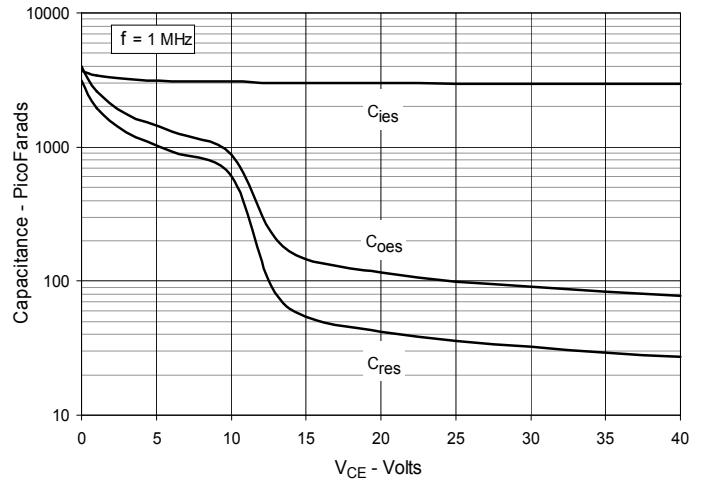
**Fig. 8. Gate Charge**



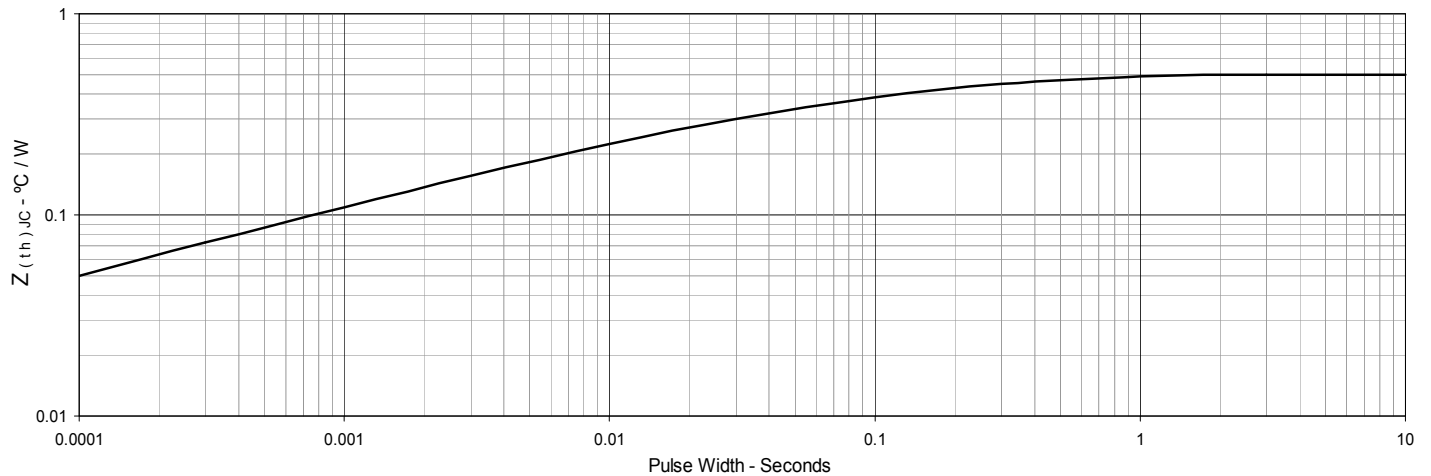
**Fig. 9. Reverse-Bias Safe Operating Area**



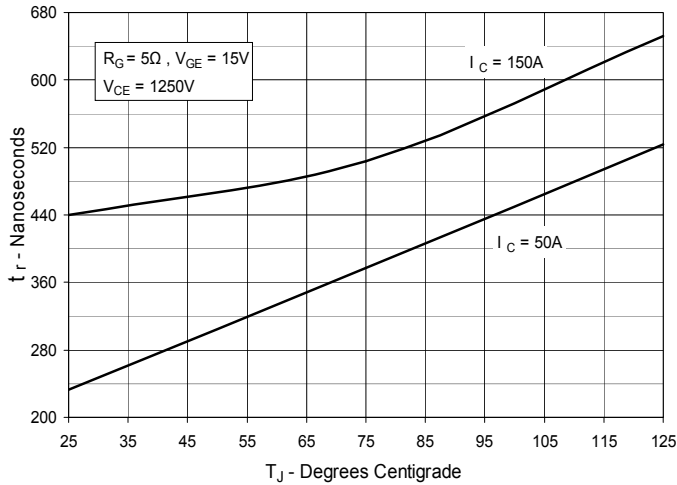
**Fig. 10. Capacitance**



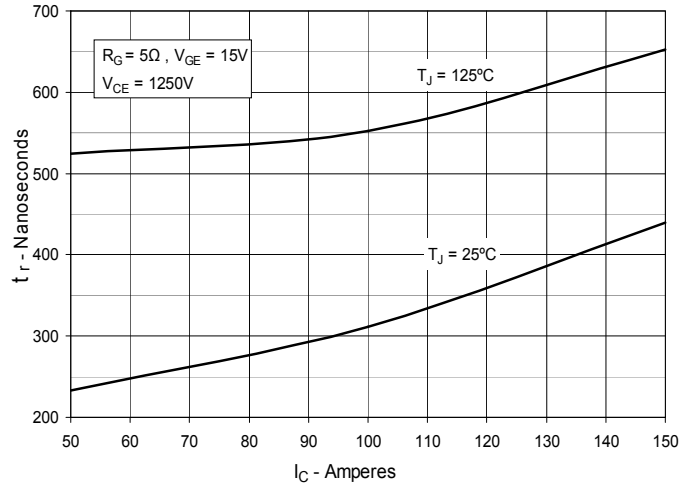
**Fig. 11. Maximum Transient Thermal Impedance**



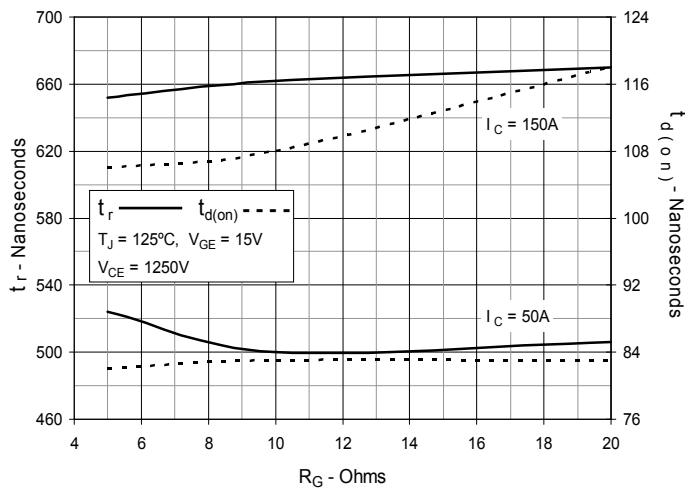
**Fig. 12. Resistive Turn-on Rise Time vs. Junction Temperature**



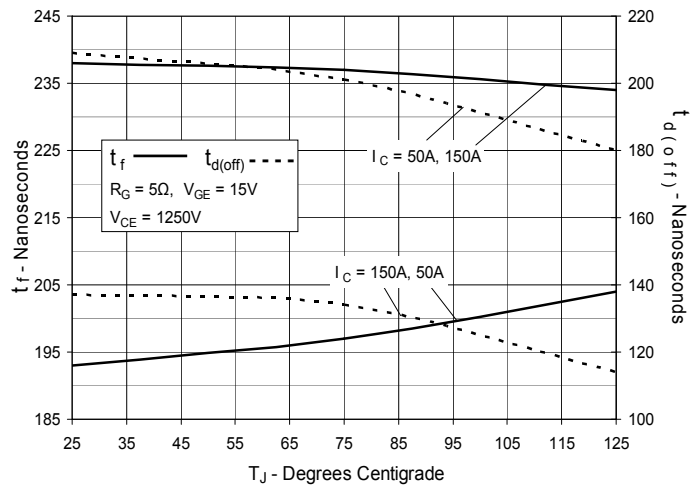
**Fig. 13. Resistive Turn-on Rise Time vs. Collector Current**



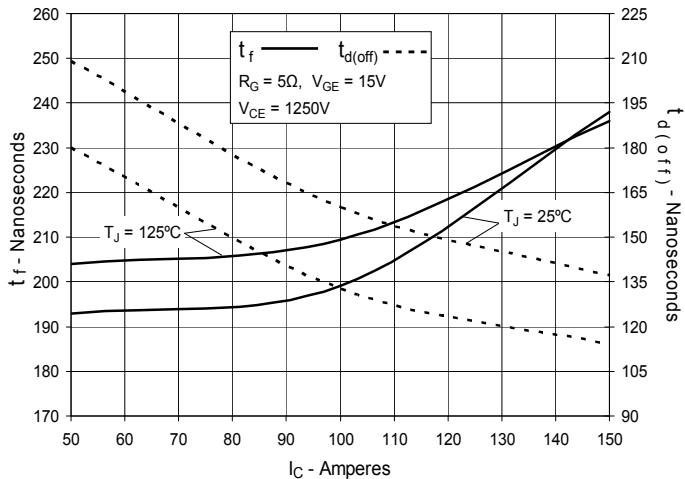
**Fig. 14. Resistive Turn-on Switching Times vs. Gate Resistance**



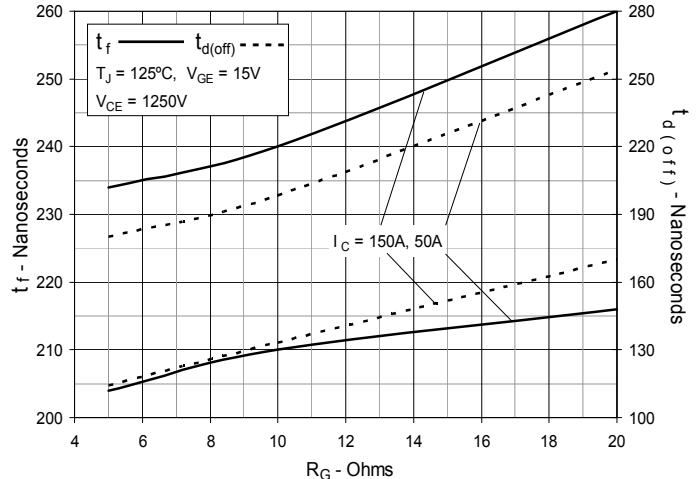
**Fig. 15. Resistive Turn-off Switching Times vs. Junction Temperature**



**Fig. 16. Resistive Turn-off Switching Times vs. Collector Current**



**Fig. 17. Resistive Turn-off Switching Times vs. Gate Resistance**





---

Disclaimer Notice - Information furnished is believed to be accurate and reliable. However, users should independently evaluate the suitability of and test each product selected for their own applications. Littelfuse products are not designed for, and may not be used in, all applications. Read complete Disclaimer Notice at [www.littelfuse.com/disclaimer-electronics](http://www.littelfuse.com/disclaimer-electronics).